

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP4065QU uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

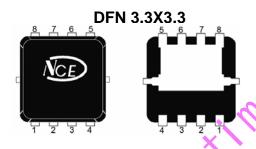
Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

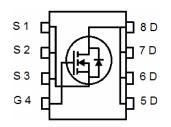
- V_{DS} =40V, I_D =65A $R_{DS(ON)}$ =2.2mΩ (typical) @ V_{GS} =10V $R_{DS(ON)}$ =3.3mΩ (typical) @ V_{GS} =4.5V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 150 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!



Top View

Bottom View



Schematic Diagram

Package Marking and Ordering Information

		1/4			
Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP4065QU	NCEP4065QU	DFN3.3X3.3-8L	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous (T _C =25°C)	I _D (T _C =25℃)	65	А
Drain Current-Continuous(T _C =100°C)	I _D (T _C =100°C)	45.5	Α
Drain Current-Continuous (T _A =25°C)	I _D (T _A =25℃)	21.5	Α
Pulsed Drain Current (Note 1)	I _{DM}	260	Α
Maximum Power Dissipation(T _C =25 ℃)	P _D (T _C =25℃)	55	W
Maximum Power Dissipation(T _A =25 ℃)	P _D (T _A =25℃)	2.1	W
Derating factor		0.44	W/℃
Single pulse avalanche energy (Note 5)	Eas	500	mJ
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 150	$^{\circ}\mathbb{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{ heta JC}$	2.3	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	60	°C/W



Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	40		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)			•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.0	1.5	2.0	V
Drain-Source On-State Resistance	Б	V _{GS} =10V, I _D =20A	-	2.2	2.8	mΩ
Diam-Source On-State Resistance	R _{DS(ON)}		-1	3.3	4.2	mΩ
Gate resistance	R_G	F=1.0MHz	-1	4.0	-	Ω
Forward Transconductance	g FS	V _{DS} =5V,I _D =20A		60	-	S
Dynamic Characteristics (Note4)		O.	•			
Input Capacitance	C _{lss}	V -20VV 20V	-	2100	-	PF
Output Capacitance	C _{oss}		-	773	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1,0lVIP12	-	15.5	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	0.0	-	7.5	-	nS
Turn-on Rise Time	tr	V _{DD} =20V,I _D =20A	-	4.0	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =1.6 Ω	-	37	-	nS
Turn-Off Fall Time	t _f		-	7.5	-	nS
Total Gate Charge	Q_g	\/ 00\/ L 00 A	-	34.8	-	nC
Gate-Source Charge	Q_{gs}	$V_{DS}=20V,I_{D}=20A,$	-	6.2		nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	5.1		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =20A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	65	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C, I_F = I_S$	-	14	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	21	-	nC
	•		-		-	•

Notes:

^{1.} Repetitive Rating: Pulse width limited by maximum junction temperature.

^{2.} The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The value in any given application depends on the user's specific board design.

^{3.} Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.

^{4.} Guaranteed by design, not subject to production

^{5.} EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=20V,VG=10V,L=0.5mH,Rg=25 Ω



Typical Electrical and Thermal Characteristics

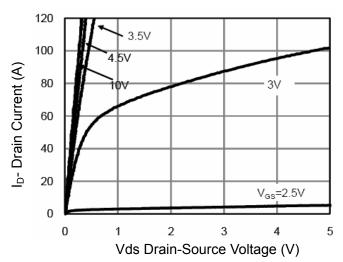


Figure 1 Output Characteristics

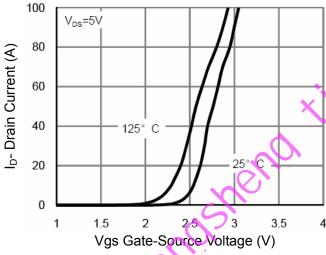


Figure 2 Transfer Characteristics

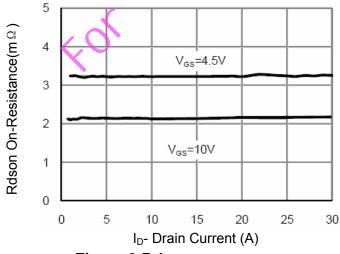


Figure 3 Rdson- Drain Current

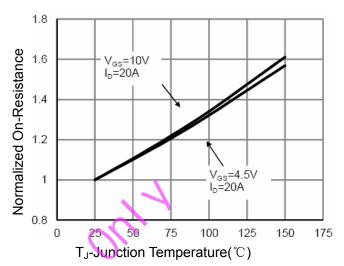


Figure 4 Rdson-Junction Temperature

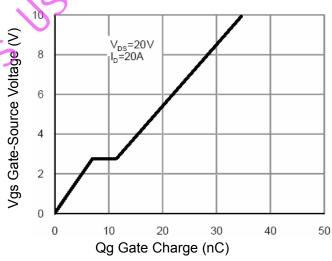


Figure 5 Gate Charge

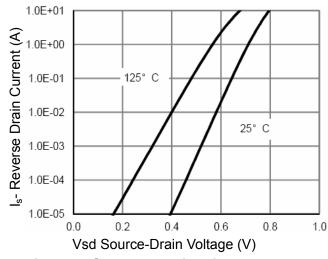


Figure 6 Source- Drain Diode Forward

10

100



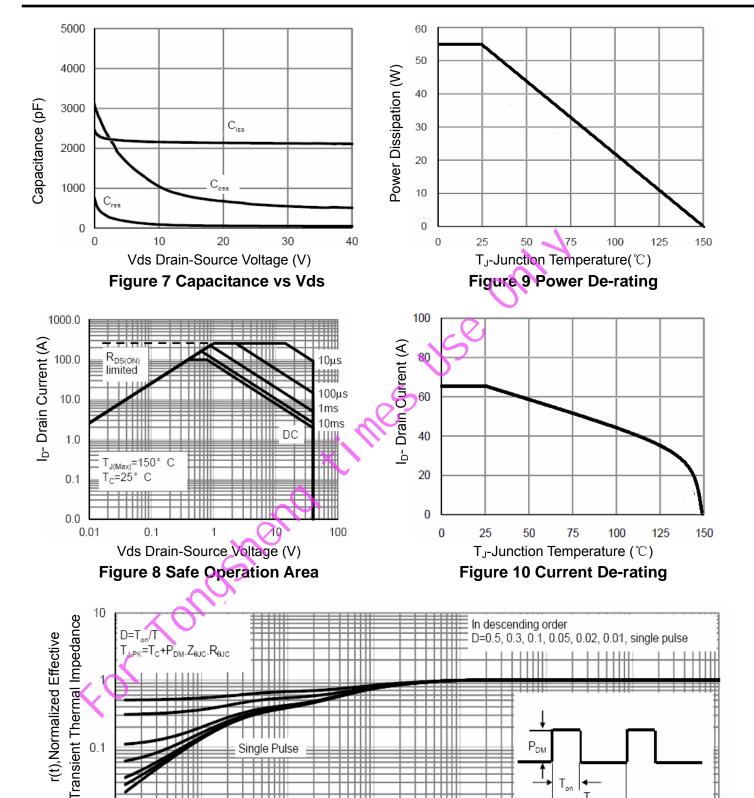


Figure 11 Normalized Maximum Transient Thermal Impedance

Square Wave Pluse Duration(sec)

0.0001

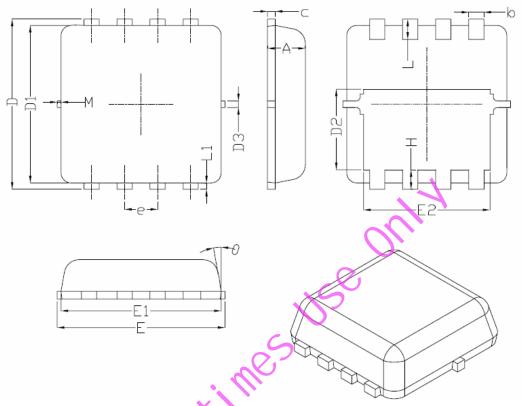
0.001

0.01

1E-05

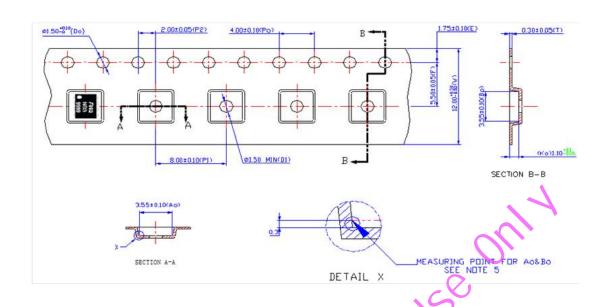


DFN3.3X3.3-8L Package Information



Symphol	Dimensions In Millimeters				
Symbol	Min.	Nom.	Max.		
A	0.70	0.75	0.80		
b	0.25	0.30	0.35		
С	0.10	0.15	0.25		
D	3.25	3.35	3.45		
D1	3.00	3.10	3.20		
D2	1.48	1.58	1.68		
D3	-	0.13	-		
√ E	3.20	3.30	3.40		
E1	3.00	3.15	3.20		
E2	2.39	2.49	2.59		
е	0.65BSC				
Н	0.30	0.39	0.50		
L	0.30	0.40	0.50		
L1	-	0.13	-		
M	*	*	0.15		
θ		10°	12 [°]		







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